

1.Description

SS029N10M6S, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V _{DSS}	100	V
I _D	210	A
R _{DS(on).typ}	2.5	mΩ

FEATURES:

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 2.9m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

APPLICATIONS:

- Switching applications
- Motor drivers
- BMS
- Synchronous rectification

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing	Quantity
SS029N10M6S	TO-263-7	SS029N10M6S	Reel	800

Schematic Diagram

